

HAT2054M

Silicon N Channel Power MOS FET
Power Switching

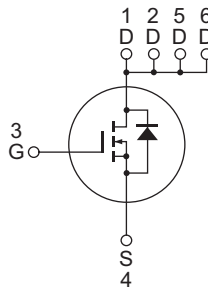
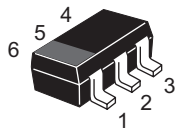
REJ03G1173-0400
(Previous: ADE-208-756B)
Rev.4.00
Sep 07, 2005

Features

- Low on-resistance
- Low drive current
- High density mounting
- 4.5 V gate drive device can be driven from 5 V source

Outline

RENESAS Package code: PTSP0006FA-A
(Package name: TSOP-6)



4 Source
3 Gate
1, 2, 5, 6 Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D ^{Note 2}	6.3	A
Drain peak current	I _{D (pulse)} ^{Note 1}	25.2	A
Body to drain diode reverse drain current	I _{DR} ^{Note 2}	6.3	A
Channel dissipation	P _{ch (pulse)} ^{Note 2}	2.0	W
	P _{ch (continuous)} ^{Note 3}	1.05	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. When using the alumina ceramic board (50 × 50 × 0.7 mm), PW ≤ 5 s, Ta = 25°C

3. When using the alumina ceramic board (50 × 50 × 0.7 mm), Ta = 25°C

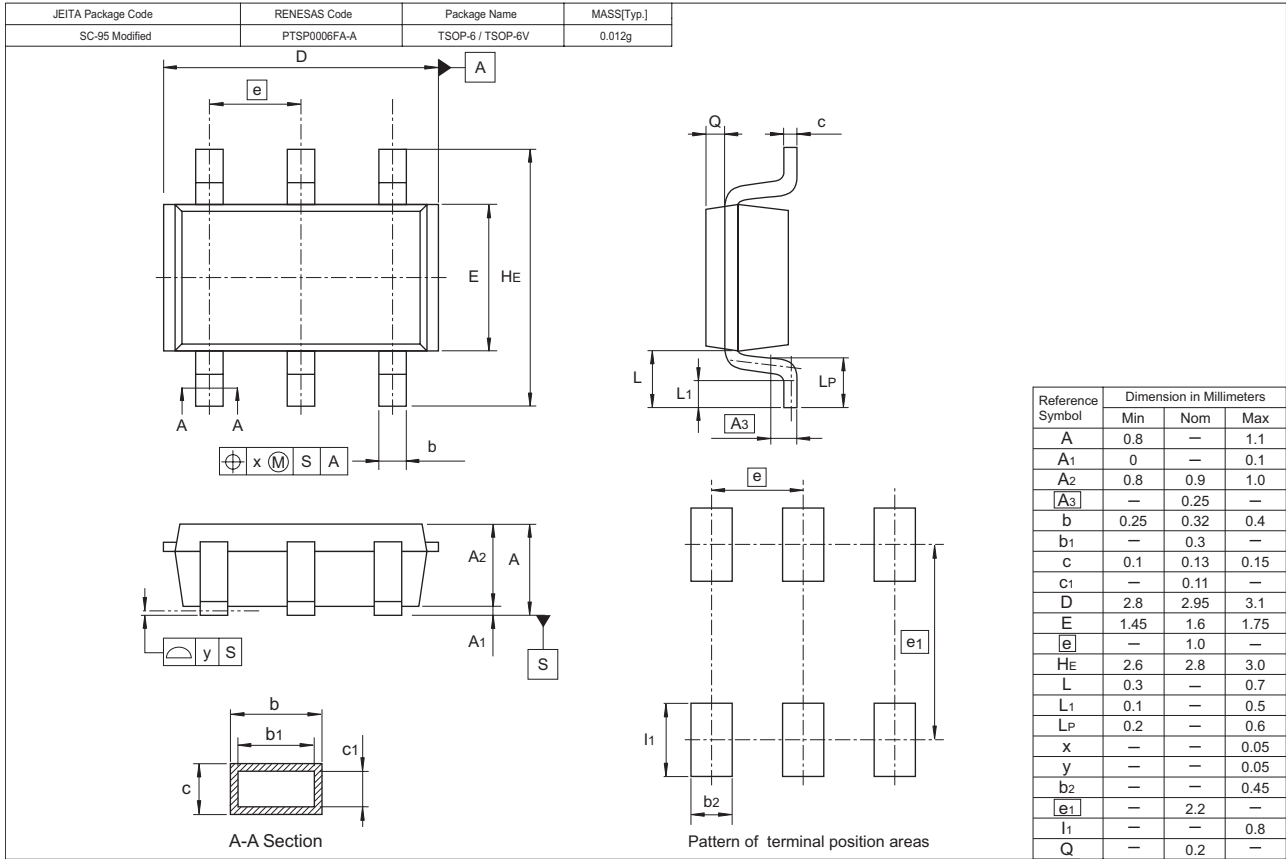
Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	30	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±0.1	μA	V _{GS} = ±20 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	1	μA	V _{DS} = 30 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS (off)}	1.0	—	2.5	V	V _{DS} = 10 V, I _D = 1 mA
Static drain to source on state resistance	R _{DS (on)}	—	26	31	mΩ	I _D = 3 A, V _{GS} = 10 V ^{Note 4}
	R _{DS (on)}	—	40	52	mΩ	I _D = 3 A, V _{GS} = 4.5 V ^{Note 4}
Forward transfer admittance	y _{fs}	4	7	—	S	I _D = 3 A, V _{DS} = 10 V ^{Note 4}
Input capacitance	C _{iss}	—	620	—	pF	V _{DS} = 10 V V _{GS} = 0 f = 1 MHz
Output capacitance	C _{oss}	—	170	—	pF	
Reverse transfer capacitance	C _{rss}	—	110	—	pF	
Turn-on delay time	t _{d (on)}	—	13	—	ns	V _{GS} = 10 V, I _D = 3 A, R _L = 3.3 Ω
Rise time	t _r	—	90	—	ns	
Turn-off delay time	t _{d (off)}	—	50	—	ns	
Fall time	t _f	—	40	—	ns	
Body to drain diode forward voltage	V _{DF}	—	0.95	—	V	I _F = 6.3 A, V _{GS} = 0 ^{Note 4}
Body to drain diode reverse recovery time	t _{rr}	—	(50)	—	ns	I _F = 6.3 A, V _{GS} = 0 di _F /dt = 20 A/μs

Note: 4. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2054M-EL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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